

ABSTRACT

A method for manufacturing a semiconductor device according to the present invention includes at least the following three steps:

- 5 (A) a step of preparing a first structure (100) including an adhesive laminate film (50) having a heat-resistant resin layer (10), a flexible resin layer (20) and an adhesive resin layer (30) in this order, and a first semiconductor component (60) adhered to the adhesive resin layer (30) and having a first terminal (65); (B) a
- 10 step of performing solder reflow processing on the first structure (100) in a state where the first semiconductor component (60) is adhered to the adhesive resin layer (30); and (C) a step of, after the step (B), peeling the heat-resistant resin layer (10) from the adhesive laminate film (50).